

Sample &

Buy



LM158-N, LM258-N, LM2904-N, LM358-N

SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

LMx58-N Low-Power, Dual-Operational Amplifiers

Technical

Documents

Features 1

- Available in 8-Bump DSBGA Chip-Sized Package, (See AN-1112, SNVA009)
- Internally Frequency Compensated for Unity Gain
- Large DC Voltage Gain: 100 dB
- Wide Bandwidth (Unity Gain): 1 MHz (Temperature Compensated)
- Wide Power Supply Range:
 - Single Supply: 3V to 32V
 - Or Dual Supplies: ±1.5V to ±16V
- Very Low Supply Current Drain (500 µA)—Essentially Independent of Supply Voltage
- Low Input Offset Voltage: 2 mV
- Input Common-Mode Voltage Range Includes . Ground
- Differential Input Voltage Range Equal to the Power Supply Voltage
- Large Output Voltage Swing
- Unique Characteristics:
 - In the Linear Mode the Input Common-Mode Voltage Range Includes Ground and the Output Voltage Can Also Swing to Ground, even though Operated from Only a Single Power Supply Voltage.
 - The Unity Gain Cross Frequency is Temperature Compensated.
 - The Input Bias Current is also Temperature Compensated.
- Advantages:
 - Two Internally Compensated Op Amps
 - Eliminates Need for Dual Supplies
 - Allows Direct Sensing Near GND and VOUT Also Goes to GND
 - Compatible with All Forms of Logic
 - Power Drain Suitable for Battery Operation

2 Applications

- Active Filters
- General Signal Conditioning and Amplification
- 4- to 20-mA Current Loop Transmitters

3 Description

Tools &

Software

The LM158 series consists of two independent, high gain, internally frequency compensated operational amplifiers which were designed specifically to operate from a single power supply over a wide range of voltages. Operation from split power supplies is also possible and the low power supply current drain is independent of the magnitude of the power supply voltage.

Support &

Community

20

Application areas include transducer amplifiers, dc gain blocks and all the conventional op-amp circuits which now can be more easily implemented in single power supply systems. For example, the LM158 series can be directly operated off of the standard 3.3-V power supply voltage which is used in digital systems and will easily provide the required interface electronics without requiring the additional ±15V power supplies.

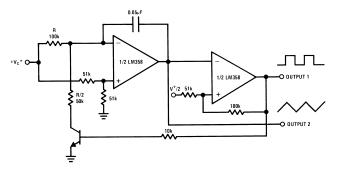
The LM358 and LM2904 are available in a chip sized package (8-Bump DSBGA) using TI's DSBGA package technology.

Device Information ⁽¹⁾								
PART NUMBER	PACKAGE	BODY SIZE (NOM)						
1 M450 N	TO-CAN (8)	9.08 mm x 9.09 mm						
LM158-N	CDIP (8)	10.16 mm x 6.502 mm						
LM258-N	TO-CAN (8)	9.08 mm x 9.09 mm						
	DSBGA (8)	1.31 mm x 1.31 mm						
LM2904-N	SOIC (8)	4.90 mm x 3.91 mm						
	PDIP (8)	9.81 mm x 6.35 mm						
	TO-CAN (8)	9.08 mm x 9.09 mm						
	DSBGA (8)	1.31 mm x 1.31 mm						
LM358-N	SOIC (8)	4.90 mm x 3.91 mm						
	PDIP (8)	9.81 mm x 6.35 mm						

Device Information $^{(1)}$

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Voltage Controlled Oscillator (VCO)





ÈXAS **ISTRUMENTS**

www.ti.com

Page

Table of Contents

1	Fea	tures 1							
2	Арр	lications 1							
3	Description1								
4	Revision History 2								
5	Pin	Configuration and Functions 3							
6	Spe	cifications 4							
	6.1	Absolute Maximum Ratings 4							
	6.2	ESD Ratings 4							
	6.3	Recommended Operating Conditions5							
	6.4	Thermal Information 5							
	6.5	Electrical Characteristics: LM158A, LM358A, LM158, LM258							
	6.6	Electrical Characteristics: LM358, LM29047							
	6.7	Typical Characteristics 9							
7	Deta	ailed Description 12							
	7.1	Overview 12							
	7.2	Functional Block Diagram 12							

	7.3	Feature Description	12
	7.4	Device Functional Modes	13
8	Арр	lication and Implementation	14
	8.1	Application Information	14
	8.2	Typical Applications	14
9	Pow	er Supply Recommendations	24
10	Lay	out	24
	10.1	Layout Guidelines	24
	10.2	Layout Example	24
11	Dev	ice and Documentation Support	25
	11.1	Related Links	25
	11.2	Trademarks	25
	11.3	Electrostatic Discharge Caution	25
	11.4	Glossary	25
12	Mec	hanical, Packaging, and Orderable	
	Info	rmation	25

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (March 2013) to Revision I

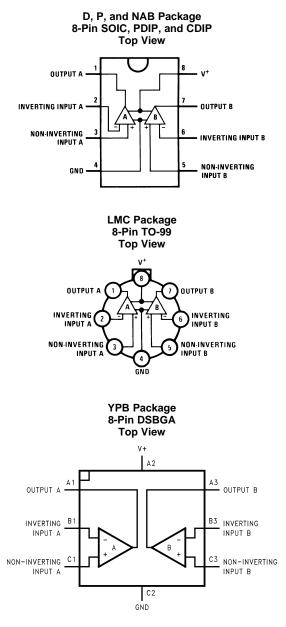
Changes from Revision G (March 2013) to Revision H

٠	Changed layout of National Data Sheet to TI format	25	
---	--	----	--

Copyright © 2000–2014, Texas Instruments Incorporated



5 Pin Configuration and Functions



Pin Functions

	PIN							
D/P/LMC NO.	DSBGA NO.	NAME	TYPE	DESCRIPTION				
1	A1	OUTA	0	Output, Channel A				
2	B1	-INA	I	Inverting Input, Channel A				
3	C1	+INA	I	Non-Inverting Input, Channel A				
4	C2	GND / V-	Р	Ground for Single supply configurations. negative supply for dual supply configurations				
5	C3	+INB	I	Output, Channel B				
6	B3	-INB	I	Inverting Input, Channel B				
7	A3	OUTB	0	Non-Inverting Input, Channel B				
8	A2	V+	Р	Positive Supply				

Copyright © 2000-2014, Texas Instruments Incorporated

SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

6 Specifications

6.1 Absolute Maximum Ratings

See (1)(2)(3).

			LM358	8, LM258, 8, LM158A, A, LM358A	L	UNIT	
			MIN	MAX	MIN	MAX	
Supply Voltage, V ⁺				32		26	V
Differential Input Voltage				32		26	V
Input Voltage			-0.3	32	-0.3	26	V
Power Dissipation ⁽⁴⁾	PDIP (P)			830		830	mW
	TO-99 (LMC)			550			mW
	SOIC (D) DSBGA (YPB)			530		530	mW
				435			mW
Output Short-Circuit to GND (One Amplifier) ⁽⁵⁾	V ⁺ ≤ 15 V and $T_A = 25^{\circ}C$			Continuous		Continuou s	
Input Current (V _{IN} < -0	.3V) ⁽⁶⁾			50		50	mA
Temperature			-55	125			°C
	PDIP Package (P): Soldering (10 se	econds)		260		260	°C
	SOIC Package (D)	Vapor Phase (60 seconds)		215		215	°C
		Infrared (15 seconds)		220		220	°C
Lead Temperature	PDIP (P): (Soldering, 10 seconds)			260		260	°C
	TO-99 (LMC): (Soldering, 10 second	ds)		300		300	°C
Storage temperature, T	stg		-65	150	-65	150	°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.

(2) Refer to RETS158AX for LM158A military specifications and to RETS158X for LM158 military specifications.

(3) If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.
(4) For operating at high temperatures, the LM358/LM358A, LM2904 must be derated based on a 125°C maximum junction temperature

- and a thermal resistance of 120°C/W for PDIP, 182°C/W for TO-99, 189°C/W for SOIC package, and 230°C/W for DSBGA, which applies for the device soldered in a printed circuit board, operating in a still air ambient. The LM258/LM258A and LM158/LM158A can be derated based on a +150°C maximum junction temperature. The dissipation is the total of both amplifiers—use external resistors, where possible, to allow the amplifier to saturate or to reduce the power which is dissipated in the integrated circuit.
- (5) Short circuits from the output to V⁺ can cause excessive heating and eventual destruction. When considering short circuits to ground, the maximum output current is approximately 40 mA independent of the magnitude of V⁺. At values of supply voltage in excess of +15 V, continuous short-circuits can exceed the power dissipation ratings and cause eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.
- (6) This input current will only exist when the voltage at any of the input leads is driven negative. It is due to the collector-base junction of the input PNP transistors becoming forward biased and thereby acting as input diode clamps. In addition to this diode action, there is also lateral NPN parasitic transistor action on the IC chip. This transistor action can cause the output voltages of the op amps to go to the V⁺voltage level (or to ground for a large overdrive) for the time duration that an input is driven negative. This is not destructive and normal output states will re-establish when the input voltage, which was negative, again returns to a value greater than -0.3 V (at 25°C).

6.2 ESD Ratings

4

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±250	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

www.ti.com



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Supply Voltage (V+ - V-):LM158. LM258, LM358	3 (±1.5)	32 (±16)	V
Supply Voltage (V+ - V-):LM2904	3 (±1.5)	26 (±13)	V
Operating Temperature: LM158	-55	125	°C
Operating Temperature: LM258	-25	85	°C
Operating Temperature: LM358	0	70	°C
Operating Temperature: LM2904	-40	85	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		LM158-N, LM258-N, LM358-N	LM158-N	LM2	904-N, LM35	8-N	UNIT
		LMC	NAB	YPB	D	Р	
				8 PINS			
$R_{\theta J A}$	Junction-to-ambient thermal resistance	155	132	230	189	120	°C/W

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics: LM158A, LM358A, LM158, LM258

 V^+ = +5.0 V, See⁽¹⁾, unless otherwise stated

	TEST CONDITIONS	LM158A LM3			LM358	LM358A		LM158, LM258			
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Input Offset Voltage	See ⁽²⁾ , T _A = 25°C		1	2		2	3		2	5	mV
Input Bias Current	$I_{IN(+)}$ or $I_{IN(-)}$, $T_A = 25^{\circ}C$,		20	50		45	100		45	150	nA
	V _{CM} = 0 V, ⁽³⁾										
Input Offset Current	$I_{IN(+)} - I_{IN(-)}, V_{CM} = 0V, T_A = 25^{\circ}C$		2	10		5	30		3	30	nA
Input Common-Mode	V ⁺ = 30 V, ⁽⁴⁾			\/ + 4							
Voltage Range	(LM2904, V ⁺ = 26V), T _A = 25°C	0		V⁺−1. 5	0		V⁺−1.5	0		V⁺−1.5	V
Supply Current	Over Full Temperature Range										
	$R_L = \infty$ on All Op Amps										
	V ⁺ = 30V (LM2904 V ⁺ = 26V)		1	2		1	2		1	2	mA
	V ⁺ = 5V		0.5	1.2		0.5	1.2		0.5	1.2	mA
Large Signal Voltage Gain	$ \begin{array}{l} V^{+=15 \ V, \ T_{A}=25^{\circ}C,} \\ R_{L}\geq 2 \ k\Omega, \ (For \ V_{O}=1 \ V \ to \\ 11 \ V) \end{array} $	50	100		25	100		50	100		V/mV
Common-Mode	T _A = 25°C,	70	05		05	05		70	05		
Rejection Ratio	$V_{CM} = 0 V$ to V ⁺ -1.5 V	70	85		65	85		70	85		dB
Power Supply	V ⁺ = 5 V to 30 V										
Rejection Ratio	(LM2904, V ⁺ = 5 V to 26 V), T _A = 25°C	65	100		65	100		65	100		dB

- (1) These specifications are limited to $-55^{\circ}C \le T_A \le +125^{\circ}C$ for the LM158/LM158A. With the LM258/LM258A, all temperature specifications are limited to $-25^{\circ}C \le T_A \le 85^{\circ}C$, the LM358/LM358A temperature specifications are limited to $0^{\circ}C \le T_A \le 70^{\circ}C$, and the LM2904 specifications are limited to $-40^{\circ}C \le T_A \le 85^{\circ}C$.
- (2) $V_0 \approx 1.4 \text{ V}, \text{ R}_S = 0 \Omega$ with V⁺ from 5 V to 30 V; and over the full input common-mode range (0 V to V⁺ -1.5 V) at 25°C. For LM2904, V⁺ from 5 V to 26 V.
- (3) The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading change exists on the input lines.
- (4) The input common-mode voltage of either input signal voltage should not be allowed to go negative by more than 0.3 V (at 25°C). The upper end of the common-mode voltage range is V⁺ −1.5 V (at 25°C), but either or both inputs can go to 32 V without damage (26 V for LM2904), independent of the magnitude of V⁺.

Copyright © 2000-2014, Texas Instruments Incorporated

SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

www.ti.com

ISTRUMENTS

EXAS

Electrical Characteristics: LM158A, LM358A, LM158, LM258 (continued)

V^+ = +5.0 V, See ⁽¹⁾ , unless otherwise s	stated
---	--------

	TED	TEST CONDITIONS		LM158/	4		LM358A		LN	1158, LN	1258	UNIT
PARAME	IER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Power Supply		V ⁺ = 5 V to 30 V										
Rejection Ratio		(LM2904, V ⁺ = 5 V to 26 V), T _A = 25°C	65	100		65	100		65	100		dB
Amplifier-to-Amp Coupling	olifier	$f = 1 \text{ kHz to } 20 \text{ kHz}, T_A = 25^{\circ}C \text{ (Input Referred), See}^{(1)}$	5)	-120			-120			-120		dB
Output Current	Source	$V_{IN}^{+} = 1 V,$										
		$V_{IN}^{-} = 0 V,$	20	40		20	40		20	40		mA
		V ⁺ = 15 V,		40		20	40		20	40		ША
		$V_0 = 2 V, T_A = 25^{\circ}C$										
	Sink	$V_{IN}^{-} = 1 V, V_{IN}^{+} = 0 V$										
		$V^+ = 15 V, T_A = 25^{\circ}C,$	10	20		10	20		10	20		mA
		V ₀ = 2 V										
		$V_{IN}^{-} = 1 V,$										
		$V_{IN}^+ = 0 V$	12	50		12	50		12	50		μA
		$T_A = 25^{\circ}C, V_O = 200 \text{ mV},$	12	50		12	50		12	50		μΑ
		V ⁺ = 15 V										
Short Circuit to Ground		$T_A = 25^{\circ}C$, See ⁽⁶⁾ , V ⁺ = 15 V	/	40	60		40	60		40	60	mA
Input Offset Volt	tage	See ⁽²⁾			4			5			7	mV
Input Offset Volt	tage Drift	$R_{S} = 0\Omega$		7	15		7	20		7		µV/°C
Input Offset Cur	rent	$I_{IN(+)} - I_{IN(-)}$			30			75			100	nA
Input Offset Cur	rent Drift	$R_{S} = 0\Omega$		10	200		10	300		10		pA/°C
Input Bias Curre	ent	I _{IN(+)} or I _{IN(-)}		40	100		40	200		40	300	nA
Input Common-I Voltage Range	Mode	V ⁺ = 30 V, See ⁽⁴⁾ (LM2904, V ⁺ = 26 V)	0		V⁺-2	0		V⁺−2	0		V⁺−2	V
Large Signal Vo	ltage Gain	V ⁺ = +15 V										
		(V _O = 1 V to 11 V)	25			15			25			V/mV
		R _L ≥2 kΩ										
Output	V _{OH}	$V^+ = +30 V$ $R_L = k\Omega$	2 26			26			26			V
Voltage		(LM2904, V ⁺ = 26 V) $\begin{array}{c} R_L = \\ 10 \text{ km} \end{array}$	27	28		27	28		27	28		V
Swing	V _{OL}	$V^+ = 5V, R_L = 10 \text{ k}\Omega$		5	20		5	20		5	20	mV
Output Current Source		$V_{IN}^{+} = +1 \text{ V}, V_{IN}^{-} = 0 \text{ V},$	10	20		10	20		10	20		mA
	a	$V^+ = 15 V, V_0 = 2 V$										
Sink		$V_{IN}^{-} = +1 V, V_{IN}^{+} = 0 V,$ $V^{+} = 15 V, V_{O} = 2 V$	10	15		5	8		5	8		mA

(5) Due to proximity of external components, insure that coupling is not originating via stray capacitance between these external parts. This typically can be detected as this type of capacitance increases at higher frequencies.

(6) Short circuits from the output to V⁺ can cause excessive heating and eventual destruction. When considering short circuits to ground, the maximum output current is approximately 40 mA independent of the magnitude of V⁺. At values of supply voltage in excess of +15 V, continuous short-circuits can exceed the power dissipation ratings and cause eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.

6



6.6 Electrical Characteristics: LM358, LM2904

 V^+ = +5.0 V, See⁽¹⁾, unless otherwise stated

PARAMETE	в	TEST CONDITIONS		LM358			LM2904		UNIT
PARAMETE	ĸ	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Input Offset Voltage		$See^{(2)}$, $T_A = 25^{\circ}C$		2	7		2	7	mV
Input Bias Current		$I_{IN(+)}$ or $I_{IN(-)}$, $T_A = 25^{\circ}C$, $V_{CM} = 0$ V, See ⁽³⁾		45	250		45	250	nA
Input Offset Current		$I_{IN(+)} - I_{IN(-)}, V_{CM} = 0 \text{ V}, T_A = 25^{\circ}\text{C}$		5	50		5	50	nA
Input Common-Mode Voltage Range		V ⁺ = 30 V, See ⁽⁴⁾ (LM2904, V ⁺ = 26 V), T _A = 25°C	0		V⁺−1. 5	0		V⁺−1.5	V
Supply Current		Over Full Temperature Range							
		R _L = ∞ on All Op Amps							
		V ⁺ = 30 V (LM2904 V ⁺ = 26 V)		1	2		1	2	mA
		V ⁺ = 5 V		0.5	1.2		0.5	1.2	mA
Large Signal Voltage		$V^+ = 15V, T_A = 25^{\circ}C,$							
Gain		$R_L \ge 2 k\Omega$, (For $V_O = 1 V$ to 11 V)	25	100		25	100		V/mV
Common-Mode		T _A = 25°C,	0	05		50	70		-ID
Rejection Ratio		$V_{CM} = 0 V \text{ to } V^+ - 1.5 V$	65	85		50	70		dB
Power Supply		V ⁺ = 5 V to 30 V	65	100		50	100		dB
Rejection Ratio		(LM2904, V ⁺ = 5 V to 26 V), $T_A = 25^{\circ}C$							
Amplifier-to-Amplifier	Coupling	f = 1 kHz to 20 kHz, $T_A = 25^{\circ}C$ (Input Referred), See ⁽⁵⁾		-120			-120		dB
Output Current	Source	$V_{IN}^{+} = 1 V,$							
		$V_{IN}^{-} = 0 V,$		40	20	20	40		~ ^
		V ⁺ = 15 V,	20	40		20	40		mA
		V _O = 2 V, T _A = 25°C							
	Sink	$V_{IN}^{-} = 1 V, V_{IN}^{+} = 0 V$							
		$V^+ = 15V, T_A = 25^{\circ}C,$	10	20		10	20		mA
		V _O = 2 V							
		$V_{IN}^{-} = 1 V,$							
		$V_{IN}^{+} = 0 V$	10	50		10	50		
		$T_A = 25^{\circ}C, V_O = 200 \text{ mV},$	12	50		12	50		μA
		V ⁺ = 15 V							
Short Circuit to Groun	d	$T_A = 25^{\circ}C, See^{(6)}, V^+ = 15 V$		40	60		40	60	mA
Input Offset Voltage		See ⁽²⁾			9			10	mV
Input Offset Voltage D	rift	$R_{\rm S} = 0 \ \Omega$		7			7		µV/°C
Input Offset Current		$I_{IN(+)} - I_{IN(-)}$			150		45	200	nA
Input Offset Current D	rift	$R_{\rm S} = 0 \ \Omega$		10			10		pA/°C
Input Bias Current		I _{IN(+)} or I _{IN(-)}		40	500		40	500	nA

(1) These specifications are limited to $-55^{\circ}C \le T_{A} \le +125^{\circ}C$ for the LM158/LM158A. With the LM258/LM258A, all temperature specifications are limited to $-25^{\circ}C \le T_A \le 85^{\circ}C$, the LM358/LM358A temperature specifications are limited to $0^{\circ}C \le T_A \le 70^{\circ}C$, and the LM2904 specifications are limited to $-40^{\circ}C \le T_A \le 85^{\circ}C$.

(2) $\dot{V}_0 \simeq 1.4 \text{ V}, \text{ R}_S = 0 \Omega$ with V⁺ from 5 V to 30 V; and over the full input common-mode range (0 V to V⁺ -1.5 V) at 25°C. For LM2904, V⁺ from 5 V to 26 V.

The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the (3) state of the output so no loading change exists on the input lines.

(4) The input common-mode voltage of either input signal voltage should not be allowed to go negative by more than 0.3 V (at 25°C). The upper end of the common-mode voltage range is V⁺ -1.5 V (at 25°C), but either or both inputs can go to 32 V without damage (26 V for LM2904), independent of the magnitude of V⁺

(5) Due to proximity of external components, insure that coupling is not originating via stray capacitance between these external parts. This typically can be detected as this type of capacitance increases at higher frequencies.

Short circuits from the output to V⁺ can cause excessive heating and eventual destruction. When considering short circuits to ground, (6)the maximum output current is approximately 40 mA independent of the magnitude of V⁺. At values of supply voltage in excess of +15 V, continuous short-circuits can exceed the power dissipation ratings and cause eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.

Copyright © 2000-2014, Texas Instruments Incorporated

SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

www.ti.com

NSTRUMENTS

Texas

Electrical Characteristics: LM358, LM2904 (continued)

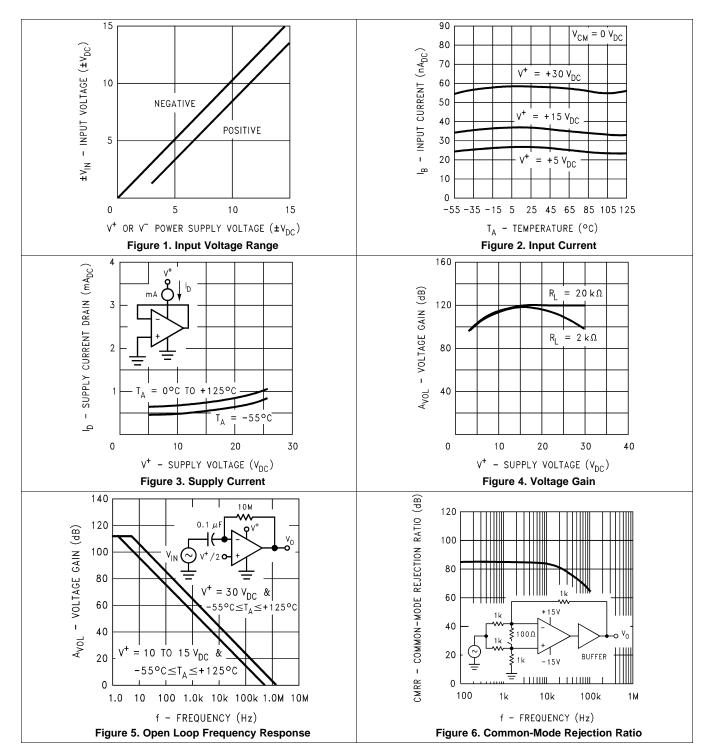
V ⁺ = +5.0 V. Se	e ⁽¹⁾ , unless otherwise stated
-----------------------------	--

DADAME		TEST CONDI	TEST CONDITIONS					LM2904	Ļ	UNIT
PARAME	IER	TEST CONDI	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
Input Common-Moo Voltage Range	le	V ⁺ = 30 V, See ⁽⁴⁾ (LM2904, V ⁺ = 26 V)				V+-2	0		V ⁺ -2	V
Large Signal Voltag	je Gain	V ⁺ = +15 V								
		(V _O = 1 V to 11 V)					15			V/mV
		R _L ≥ 2 kΩ								
Output	V _{OH}	V ⁺ = 30 V	$R_L = 2 k\Omega$	26			22			V
Voltage		(LM2904, V ⁺ = 26 V)	$R_L = 10 \ k\Omega$	27	28		23	24		V
Swing	V _{OL}	$V^+ = 5 V$, $R_L = 10 k\Omega$			5	20		5	100	mV
Output Current	Source	$V_{IN}^{+} = 1 \text{ V}, V_{IN}^{-} = 0 \text{ V},$	10	20		40	20			
		V ⁺ = 15 V, V _O = 2 V		10	20		10	20		mA
Sink		$V_{IN}^{-} = 1 V, V_{IN}^{+} = 0 V,$	5	0			0			
		$V^+ = 15 V, V_0 = 2 V$		8		5	8		mA	

8



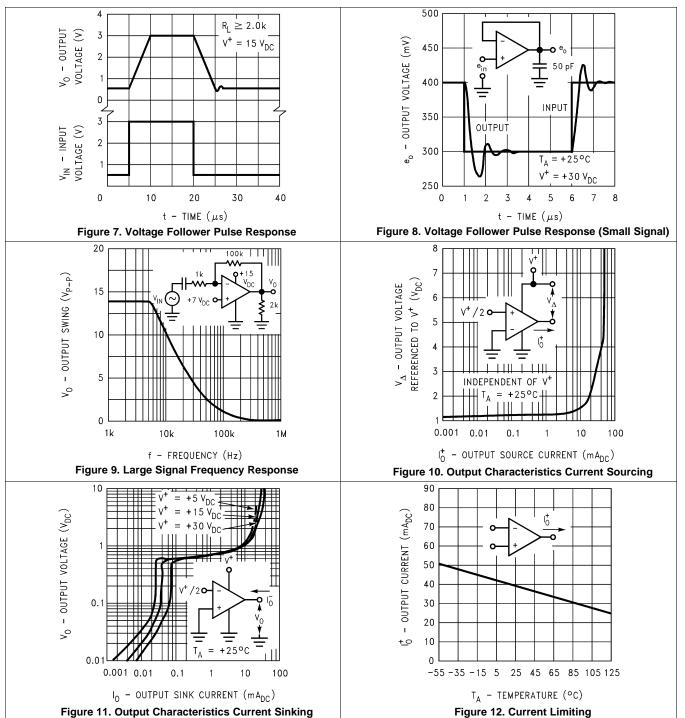
6.7 Typical Characteristics



LM158-N, LM258-N, LM2904-N, LM358-N

SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

Typical Characteristics (continued)

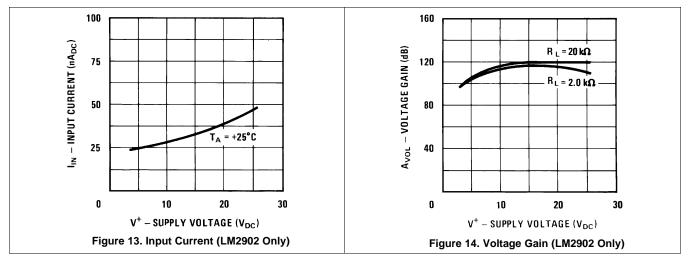




LM158-N, LM258-N, LM2904-N, LM358-N

SNOSBT3I – JANUARY 2000 – REVISED DECEMBER 2014

Typical Characteristics (continued)



ISTRUMENTS

7 Detailed Description

7.1 Overview

The LM158 series are operational amplifiers which can operate with only a single power supply voltage, have true-differential inputs, and remain in the linear mode with an input common-mode voltage of 0 V_{DC} . These amplifiers operate over a wide range of power supply voltage with little change in performance characteristics. At 25°C amplifier operation is possible down to a minimum supply voltage of 2.3 V_{DC} .

Large differential input voltages can be easily accommodated and, as input differential voltage protection diodes are not needed, no large input currents result from large differential input voltages. The differential input voltage may be larger than V⁺ without damaging the device. Protection should be provided to prevent the input voltages from going negative more than $-0.3 V_{DC}$ (at 25°C). An input clamp diode with a resistor to the IC input terminal can be used.

7.2 Functional Block Diagram

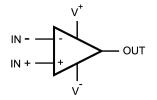


Figure 15. (Each Amplifier)

7.3 Feature Description

The amplifier's differential inputs consist of a non-inverting input (+IN) and an inverting input (–IN). The amplifier amplifies only the difference in voltage between the two inpus, which is called the differential input voltage. The output voltage of the op-amp Vout is given by Equation 1:

VOUT = AOL (IN+ - IN-)

where

• AOL is the open-loop gain of the amplifier, typically around 100dB (100,000x, or 10uV per Volt). (1)

To reduce the power supply current drain, the amplifiers have a class A output stage for small signal levels which converts to class B in a large signal mode. This allows the amplifiers to both source and sink large output currents. Therefore both NPN and PNP external current boost transistors can be used to extend the power capability of the basic amplifiers. The output voltage needs to raise approximately 1 diode drop above ground to bias the on-chip vertical PNP transistor for output current sinking applications.

For ac applications, where the load is capacitively coupled to the output of the amplifier, a resistor should be used, from the output of the amplifier to ground to increase the class A bias current and prevent crossover distortion. Where the load is directly coupled, as in dc applications, there is no crossover distortion.

Capacitive loads which are applied directly to the output of the amplifier reduce the loop stability margin. Values of 50 pF can be accommodated using the worst-case non-inverting unity gain connection. Large closed loop gains or resistive isolation should be used if larger load capacitance must be driven by the amplifier.

The bias network of the LM158 establishes a drain current which is independent of the magnitude of the power supply voltage over the range of 3 V_{DC} to 30 V_{DC} .

Output short circuits either to ground or to the positive power supply should be of short time duration. Units can be destroyed, not as a result of the short circuit current causing metal fusing, but rather due to the large increase in IC chip power dissipation which will cause eventual failure due to excessive junction temperatures. Putting direct short-circuits on more than one amplifier at a time will increase the total IC power dissipation to destructive levels, if not properly protected with external dissipation limiting resistors in series with the output leads of the amplifiers. The larger value of output source current which is available at 25°C provides a larger output current capability at elevated temperatures (see *Typical Characteristics*) than a standard IC op amp.



7.4 Device Functional Modes

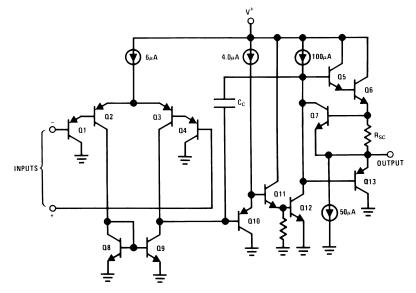


Figure 16. Schematic Diagram

The circuits presented in the *Typical Single-Supply Applications* emphasize operation on only a single power supply voltage. If complementary power supplies are available, all of the standard op-amp circuits can be used. In general, introducing a pseudo-ground (a bias voltage reference of $V^+/2$) will allow operation above and below this value in single power supply systems. Many application circuits are shown which take advantage of the wide input common-mode voltage range which includes ground. In most cases, input biasing is not required and input voltages which range to ground can easily be accommodated.



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

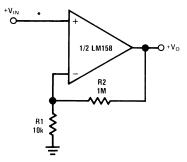
8.1 Application Information

The LM158 family bring performance, economy, and ease-of-use to a wide variety of op-amp applications.

8.2 Typical Applications

8.2.1 Noninverting DC Gain

Figure 17 shows a high input impedance non-inverting circuit. This circuit gives a closed-loop gain equal to the ratio of the sum of R1 and R2 to R1 and a closed-loop 3 dB bandwidth equal to the amplifier unity-gain frequency divided by the closed-loop gain. This design has the benefit of a very high input impedance, which is equal to the differential input impedance multiplied by loop gain. (Open loop gain/Closed loop gain.) In DC coupled applications, input impedance is not as important as input current and its voltage drop across the source resistance. Note that the amplifier output will go into saturation if the input is allowed to float. This may be important if the amplifier must be switched from source to source.



*R not needed due to temperature independent IIN

Figure 17. Non-Inverting DC Gain (0-V Output)

8.2.1.1 Design Requirements

For this example application, the supply voltage is +5V, and 100x±5% of noninverting gain is necessary. Signal input impedance is approx $10k\Omega$.

8.2.1.2 Detailed Design Procedure

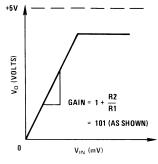
Using the equation for a non-inverting amplifier configuration ; G = 1 + R2/R1, set R1 to $10k\Omega$, and R2 to 99x the value of R1, which would be $990k\Omega$. Replacing the $990k\Omega$ with a $1M\Omega$ will result in a gain of 101, which is within the desired gain tolerance.

The gain-frequency characteristic of the amplifier and its feedback network must be such that oscillation does not occur. To meet this condition, the phase shift through amplifier and feedback network must never exceed 180° for any frequency where the gain of the amplifier and its feedback network is greater than unity. In practical applications, the phase shift should not approach 180° since this is the situation of conditional stability. Obviously the most critical case occurs when the attenuation of the feedback network is zero.



Typical Applications (continued)

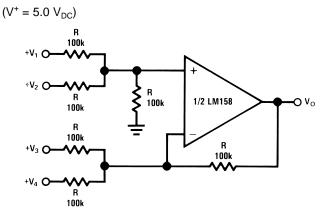
8.2.1.3 Application Curve





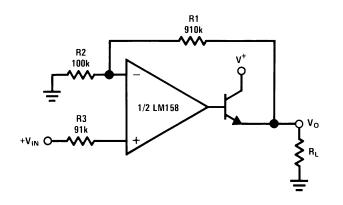
8.2.2 System Examples

8.2.2.1 Typical Single-Supply Applications



Where: $V_0 = V_1 + V_2 - V_3 - V_4$ $(V_1 + V_2) \ge (V_3 + V_4)$ to keep $V_0 > 0 V_{DC}$

Figure 19. DC Summing Amplifier $(V_{IN'S} \ge 0 V_{DC} \text{ and } V_O \ge 0 V_{DC})$

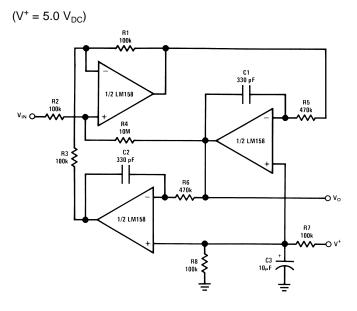


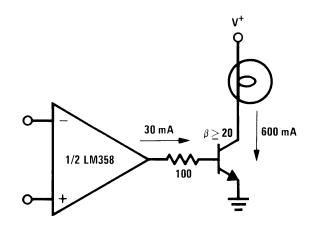
 $V_{O} = 0 V_{DC}$ for $V_{IN} = 0 V_{DC}$ $A_{V} = 10$

Figure 20. Power Amplifier



Typical Applications (continued)





 $f_o = 1 \text{ kHz}$

Q = 50

 $A_v = 100 (40 \text{ dB})$

Figure 21. "BI-QUAD" RC Active Bandpass Filter

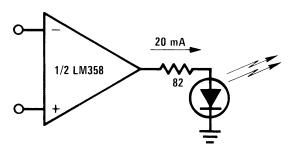
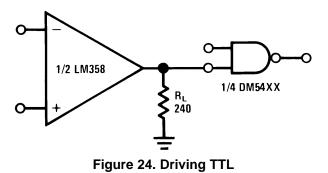


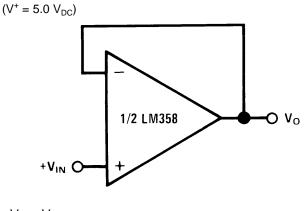
Figure 23. LED Driver

Figure 22. Lamp Driver





Typical Applications (continued)



 $V_{O} = V_{IN}$

Figure 25. Voltage Follower

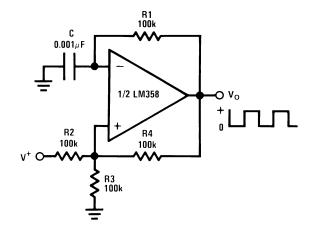
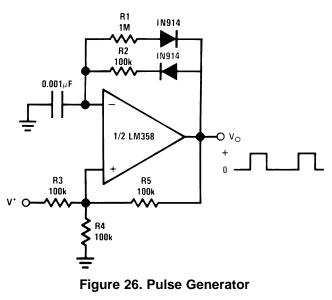


Figure 27. Squarewave Oscillator



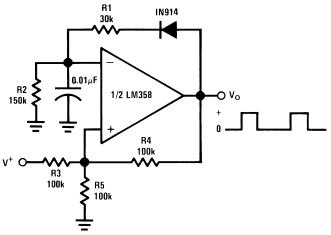
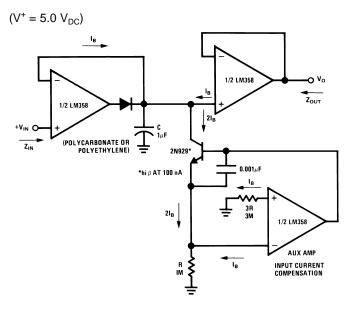
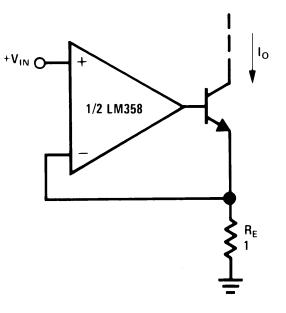


Figure 28. Pulse Generator



Typical Applications (continued)





HIGH Z_{IN} LOW Z_{OUT}

Figure 29. Low Drift Peak Detector

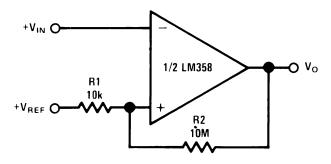
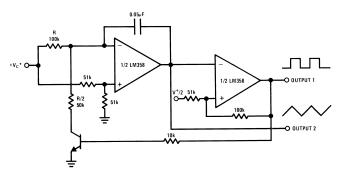


Figure 31. Comparator with Hysteresis

Figure 30. High Compliance Current Sink

 $I_0 = 1 \text{ amp/volt } V_{IN}$

(Increase R_E for I_O small)



*WIDE CONTROL VOLTAGE RANGE: 0 V_{DC} \leq V_C \leq 2 (V⁺ –1.5V _{DC})

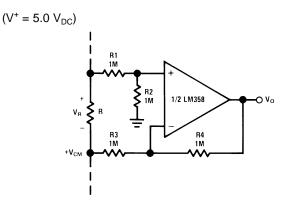
Figure 32. Voltage Controlled Oscillator (VCO)

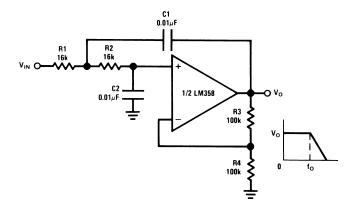
18 Submit Documentation Feedback

Product Folder Links: LM158-N LM258-N LM2904-N LM358-N



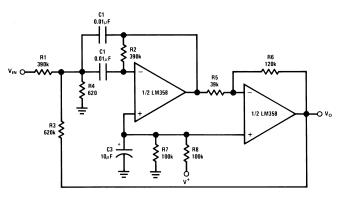
Typical Applications (continued)



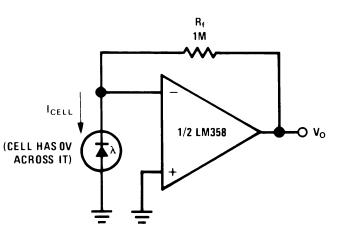


 $f_o = 1 \text{ kHz}$ Q = 1 $A_V = 2$









 $f_o = 1 \text{ kHz}$ Q = 25

Figure 35. Bandpass Active Filter

Figure 36. Photo Voltaic-Cell Amplifier

LM158-N, LM258-N, LM2904-N, LM358-N SNOSBT3I – JANUARY 2000 – REVISED DECEMBER 2014

Typical Applications (continued)

 $(V^+ = 5.0 V_{DC})$

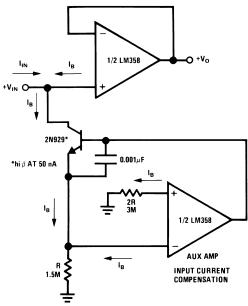


Figure 37. Using Symmetrical Amplifiers to Reduce Input Current (General Concept)

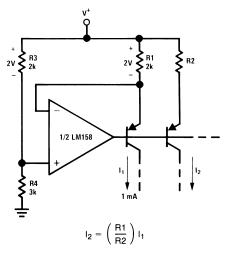
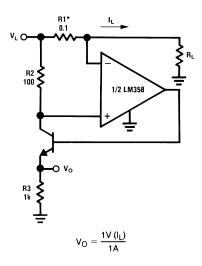


Figure 38. Fixed Current Sources



Typical Applications (continued)

 $(V^+ = 5.0 V_{DC})$



*(Increase R1 for I_L small) $V_L \le V^+ -2V$

Figure 39. Current Monitor

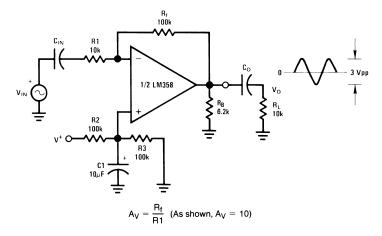
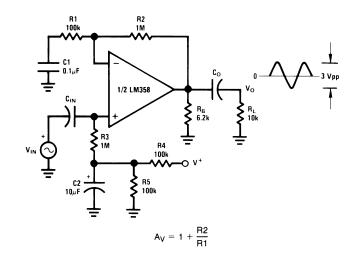


Figure 40. AC Coupled Inverting Amplifier



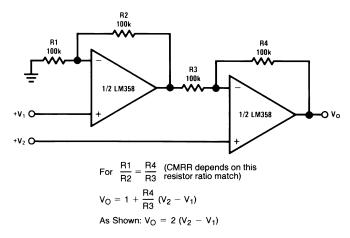
Typical Applications (continued)

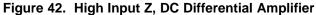
 $(V^+ = 5.0 V_{DC})$

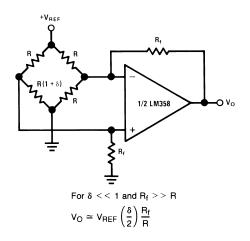


 $A_v = 11$ (As Shown)







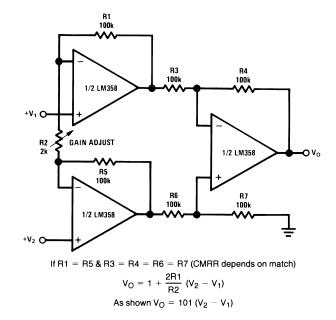






Typical Applications (continued)

 $(V^+ = 5.0 V_{DC})$





SNOSBT3I-JANUARY 2000-REVISED DECEMBER 2014

9 Power Supply Recommendations

For proper operation, the power supplies must be properly decoupled. For decoupling the supply pins it is suggested that 10 nF capacitors be placed as close as possible to the op-amp power supply pins. For single supply, place a capacitor between V+ and V-supply leads. For dual supplies, place one capacitor between V+ and ground, and one capacitor between V- and ground.

Precautions should be taken to insure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a test socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

10 Layout

10.1 Layout Guidelines

For single-ended supply configurations, the V+ pin should be bypassed to ground with a low ESR capacitor. The optimum placement is closest to the V+ pin. Care should be taken to minimize the loop area formed by the bypass capacitor connection between V+ and ground. The ground pin should be connected to the PCB ground plane at the pin of the device. The feedback components should be placed as close to the device as possible to minimize stray parasitics.

For dual supply configurations, both the V+ pin and V- pin should be bypassed to ground with a low ESR capacitor. The optimum placement is closest to the corresponding supply pin. Care should be taken to minimize the loop area formed by the bypass capacitor connection between V+ or V- and ground. The feedback components should be placed as close to the device as possible to minimize stray parasitics.

For both configurations, as ground plane underneath the device is recommended.

10.2 Layout Example

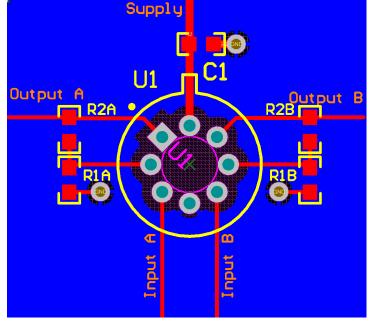


Figure 45. Layout Example



www.ti.com



11 Device and Documentation Support

11.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LM158-N	Click here	Click here	Click here	Click here	Click here
LM258-N	Click here	Click here	Click here	Click here	Click here
LM2904-N	Click here	Click here	Click here	Click here	Click here
LM358-N	Click here	Click here	Click here	Click here	Click here

Table 1. Related Links

11.2 Trademarks

All trademarks are the property of their respective owners.

11.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



19-Mar-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
LM158AH	(1) ACTIVE	TO-99	LMC	8	500	(2) TBD	(6) Call TI	(3) Call TI	-55 to 125	(4/5) (LM158AH ~ LM158AH)	Samples
LM158AH/NOPB	ACTIVE	TO-99	LMC	8	500	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	-55 to 125	(LM158AH ~ LM158AH)	Samples
LM158H	ACTIVE	TO-99	LMC	8	500	TBD	Call TI	Call TI	-55 to 125	(LM158H ~ LM158H)	Samples
LM158H/NOPB	ACTIVE	TO-99	LMC	8	500	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	-55 to 125	(LM158H ~ LM158H)	Samples
LM158J	ACTIVE	CDIP	NAB	8	40	TBD	Call TI	Call TI	-55 to 125	LM158J	Samples
LM258H	ACTIVE	TO-99	LMC	8	500	TBD	Call TI	Call TI	-25 to 85	(LM258H ~ LM258H)	Samples
LM258H/NOPB	ACTIVE	TO-99	LMC	8	500	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	-25 to 85	(LM258H ~ LM258H)	Samples
LM2904ITP/NOPB	ACTIVE	DSBGA	YPB	8	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	A 09	Samples
LM2904ITPX/NOPB	ACTIVE	DSBGA	YPB	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	A 09	Samples
LM2904M	NRND	SOIC	D	8	95	TBD	Call TI	Call TI	-40 to 85	LM 2904M	
LM2904M/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LM 2904M	Samples
LM2904MX	NRND	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 85	LM 2904M	
LM2904MX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	LM 2904M	Samples
LM2904N/NOPB	ACTIVE	PDIP	Ρ	8	40	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	-40 to 85	LM 2904N	Samples
LM358AM	NRND	SOIC	D	8	95	TBD	Call TI	Call TI	0 to 70	LM 358AM	
LM358AM/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM 358AM	Samples
LM358AMX	NRND	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70	LM 358AM	



PACKAGE OPTION ADDENDUM

19-Mar-2015

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LM358AMX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM 358AM	Samples
LM358AN/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LM 358AN	Samples
LM358H/NOPB	ACTIVE	TO-99	LMC	8	500	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	0 to 70	(LM358H ~ LM358H)	Samples
LM358M	NRND	SOIC	D	8	95	TBD	Call TI	Call TI	0 to 70	LM 358M	
LM358M/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM 358M	Samples
LM358MX	NRND	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70	LM 358M	
LM358MX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM 358M	Samples
LM358N/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LM 358N	Samples
LM358TP/NOPB	ACTIVE	DSBGA	YPB	8	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	0 to 70	A 07	Samples
LM358TPX/NOPB	ACTIVE	DSBGA	YPB	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	0 to 70	A 07	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)



19-Mar-2015

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



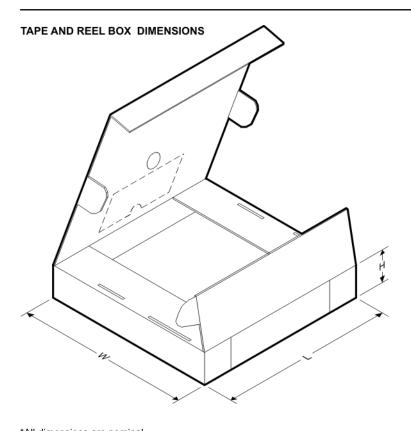
*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM2904ITP/NOPB	DSBGA	YPB	8	250	178.0	8.4	1.5	1.5	0.66	4.0	8.0	Q1
LM2904ITPX/NOPB	DSBGA	YPB	8	3000	178.0	8.4	1.5	1.5	0.66	4.0	8.0	Q1
LM2904MX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM2904MX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM358AMX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM358AMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM358MX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM358MX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LM358TP/NOPB	DSBGA	YPB	8	250	178.0	8.4	1.5	1.5	0.66	4.0	8.0	Q1
LM358TPX/NOPB	DSBGA	YPB	8	3000	178.0	8.4	1.5	1.5	0.66	4.0	8.0	Q1

Texas Instruments

www.ti.com

PACKAGE MATERIALS INFORMATION

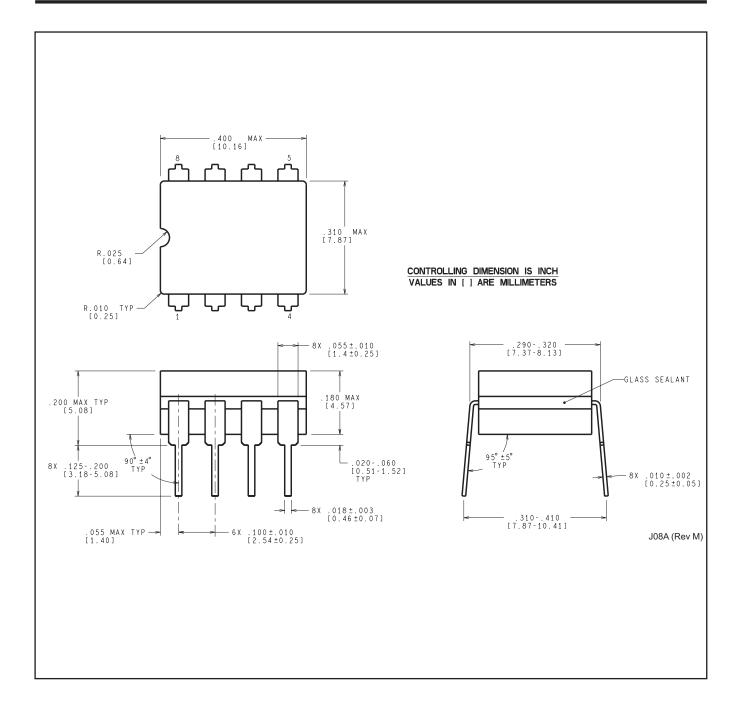
7-Oct-2014



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM2904ITP/NOPB	DSBGA	YPB	8	250	210.0	185.0	35.0
LM2904ITPX/NOPB	DSBGA	YPB	8	3000	210.0	185.0	35.0
LM2904MX	SOIC	D	8	2500	367.0	367.0	35.0
LM2904MX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LM358AMX	SOIC	D	8	2500	367.0	367.0	35.0
LM358AMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LM358MX	SOIC	D	8	2500	367.0	367.0	35.0
LM358MX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LM358TP/NOPB	DSBGA	YPB	8	250	210.0	185.0	35.0
LM358TPX/NOPB	DSBGA	YPB	8	3000	210.0	185.0	35.0

MECHANICAL DATA

NAB0008A





D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



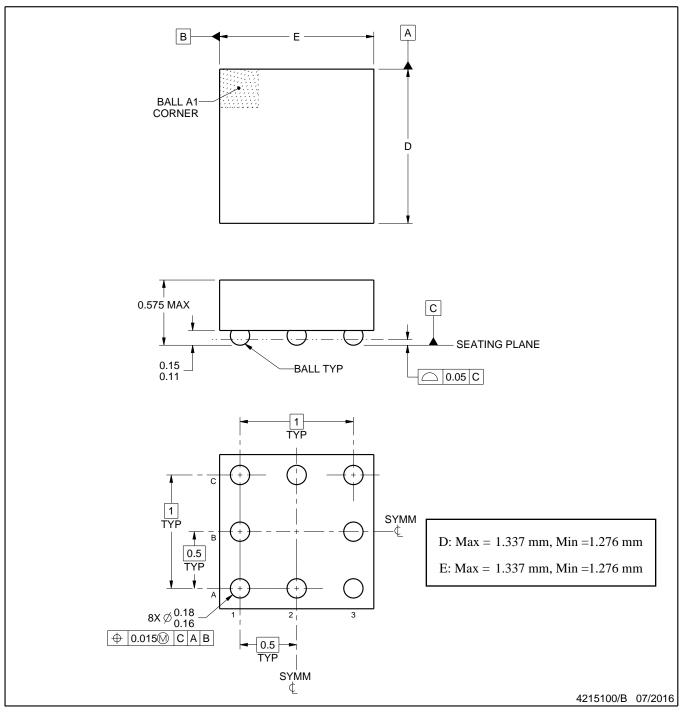
YPB0008



PACKAGE OUTLINE

DSBGA - 0.575 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.

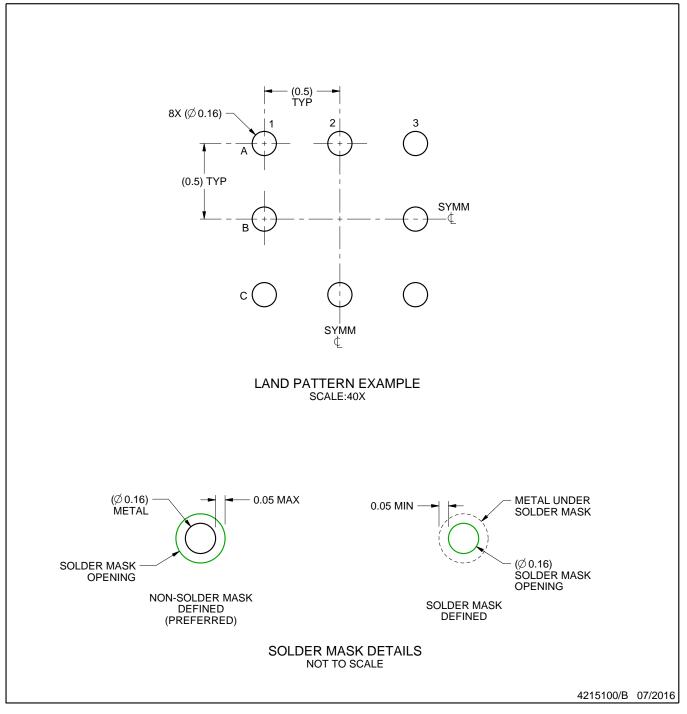


YPB0008

EXAMPLE BOARD LAYOUT

DSBGA - 0.575 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

 Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).

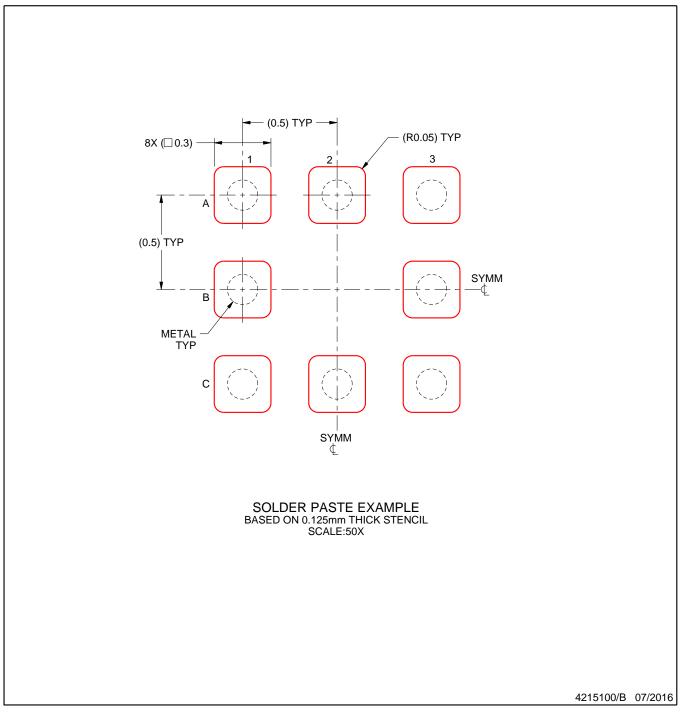


YPB0008

EXAMPLE STENCIL DESIGN

DSBGA - 0.575 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



LMC (O-MBCY-W8)

METAL CYLINDRICAL PACKAGE



- B. This drawing is subject to change without notice.
 - C. Leads in true position within 0.010 (0,25) R @ MMC at seating plane.
 - D. Pin numbers shown for reference only. Numbers may not be marked on package.
 - E. Falls within JEDEC MO-002/TO-99.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ctivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2016, Texas Instruments Incorporated